

PTO/SB/08A

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

Sheet 1 of 4

Application Number.: Unassigned  
 Filing Date: Herewith  
 First Named Inventor: Toshiharu Furukawa  
 Art Unit: Unassigned  
 Examiner Name: Unassigned  
 Attorney Docket Number.: ROC920030271US1

**U.S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns or Lines Where Relevant Passages or Figs. Appear
		Number - Kind Code <sup>2</sup> (if known)			
DN		US - 6.423.583 B1	07-23-2002	Avouris et al.	
		US - 6.515.325 B1	02-04-2003	Farnworth et al.	
		US - 2003/0168683 A1	09-11-2003	Farnworth et al.	
		US - 2003/0170930 A1	09-11-2003	Choi et al.	
		US - 2003/0178617 A1	09-25-2003	Appenzeller et al.	
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		Country <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)				

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<sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language translation is attached.

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ON		P. HARRIS, "Carbon Nanotubes and Related Structures," Cambridge University Press, 1999.	
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 Examiner Name: Unassigned  
 Attorney Docket Number.: ROC920030271US1

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ON		V. DERYCKE et al., "Carbon Nanotube Inter- and Intramolecular Logic Gates," Nano Letters, xxx, Vol. 0, No. 0, A-D, received August 16, 2001.	
		P. COLLINS et al., "Nanotubes for Electronics," Scientific American, December 2000, pp. 62-69.	
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		Z. REN et al., "Synthesis of Large Arrays of Well-Aligned Carbon Nanotubes on Glass," Science, Vol. 282, November 6, 1998, pp. 1105-1107.	
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# **INFORMATION DISCLOSURE STATEMENT BY APPLICANT** ( Not for submission under 37 CFR 1.99)

Application Number	10777576
Filing Date	2004-02-12
First Named Inventor	Toshiharu Furukawa
Art Unit	2811
Examiner Name	Ori Nadav
Attorney Docket Number	ROC920030271US

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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> ( Not for submission under 37 CFR 1.99)	Application Number		10777576
	Filing Date		2004-02-12
	First Named Inventor	Toshiharu Furukawa	
	Art Unit	2811	
	Examiner Name	Ori Nadav	
	Attorney Docket Number	ROC920030271US	

ON	1	THOMAS RUECKES, ET AL., Carbon Nanotube-Based Nonvolatile Random Access Memory for Molecular Computing, Science magazine, July 7, 2000, Pages 94-97, Vol. 289.	<input type="checkbox"/>
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